

# RB521S-30

## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

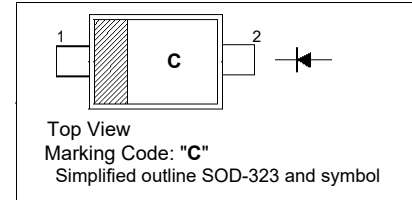
for low current rectification and high speed switching applications

### Features

- Extremely small surface mounting type

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Mean Rectifying Current	I <sub>O</sub>	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I <sub>FSM</sub>	1	A
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	T <sub>stg</sub>	- 40 to + 125	°C

### Characteristics at T<sub>a</sub> = 25°C

Parameter	Symbol	Max	Unit
Forward Voltage at I <sub>F</sub> = 200 mA	V <sub>F</sub>	0.5	V
Reverse Current at V <sub>R</sub> = 10 V	I <sub>R</sub>	30	μA

### Electrical characteristic curves (T<sub>a</sub>=25° C)

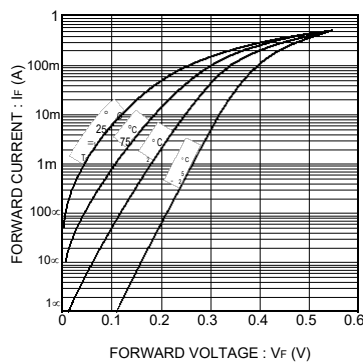


Fig. 1 Forward characteristics

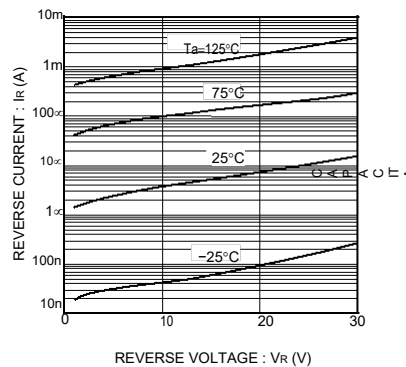


Fig. 2 Reverse characteristics

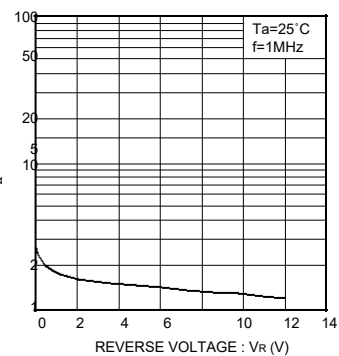


Fig. 3 Capacitance between terminals characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

